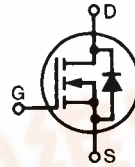


HiPerFET™ IXFK 180N10 Power MOSFETs IXFX 180N10

$V_{DSS} = 100\text{ V}$
 $I_{D25} = 180\text{ A}$
 $R_{DS(on)} = 8\text{ m}\Omega$
 $t_{rr} \leq 250\text{ ns}$

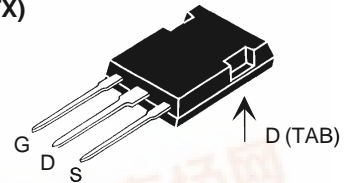
Single MOSFET Die

Preliminary data sheet

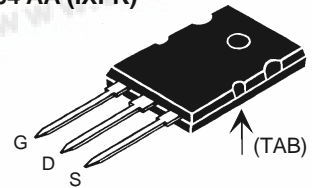


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	100	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$ (MOSFET chip capability)	180	A
$I_{D(RMS)}$	External lead (current limit)	76	A
I_{DM}	$T_C = 25^\circ\text{C}$, Note 1	720	A
I_{AR}	$T_C = 25^\circ\text{C}$	180	A
E_{AR}	$T_C = 25^\circ\text{C}$	60	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	3	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2\ \Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	560	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	TO-264	0.9/6 Nm/lb.in.
Weight		PLUS 247	6 g
		TO-264	10 g

PLUS 247™ (IXFX)



TO-264 AA (IXFK)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- Fast intrinsic rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

Advantages

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

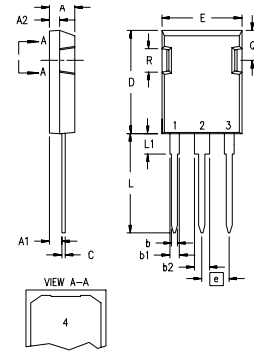
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 3\text{ mA}$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8\text{ mA}$	2.0		V
I_{GSS}	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		100 μA
		$T_J = 125^\circ\text{C}$		2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Note 1			8 m Ω



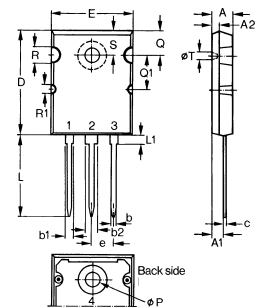
Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 60\text{ A}$ Note 2	60	90	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		9100	pF
C_{oss}			3200	pF
C_{rss}			1660	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		50	ns
t_r			90	ns
$t_{d(off)}$			140	ns
t_f			65	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		360	nC
Q_{gs}			65	nC
Q_{gd}			190	nC
R_{thJC}			0.22	K/W
R_{thCK}		0.15		K/W

Source-Drain Diode		Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			180 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			720 A
V_{SD}	$I_F = 100\text{ A}, V_{GS} = 0\text{ V}, \text{ Note 1}$			1.5 V
t_{rr}	$I_F = 50\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 50\text{ V}$			250 ns
Q_{RM}			1.1	μC
I_{RM}			13	A

Note: 1. Pulse width limited by T_{JM}
 2. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

PLUS247™ (IXFX) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190

TO-264 AA (IXFK) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A ₁	2.54	2.89	.100	.114
A ₂	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b ₁	2.39	2.69	.094	.106
b ₂	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

Figure 1. Output Characteristics at 25°C

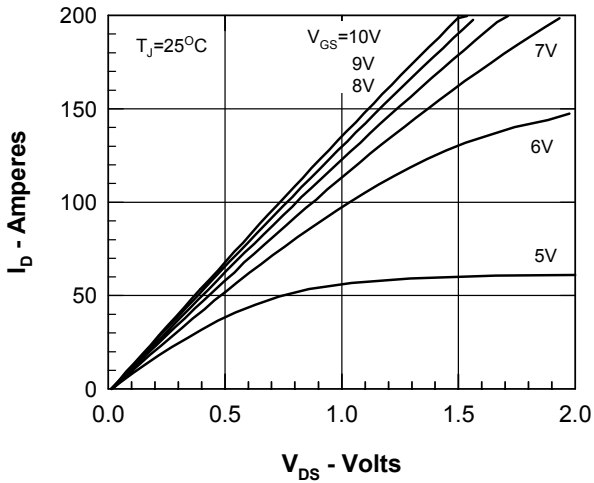


Figure 2. Output Characteristics at 125°C

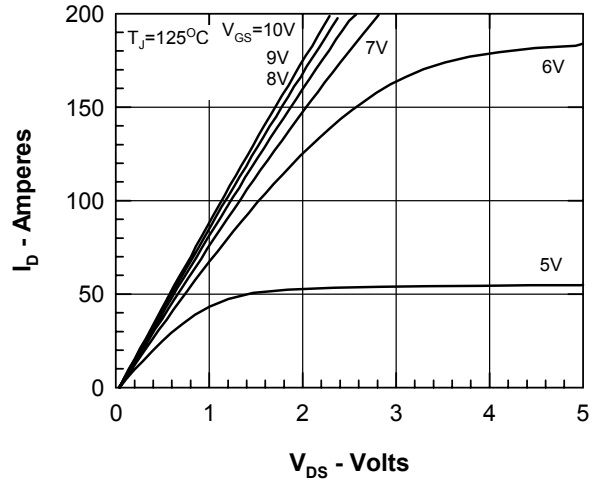


Figure 3. $R_{DS(on)}$ normalized to 15A/25°C vs. I_D

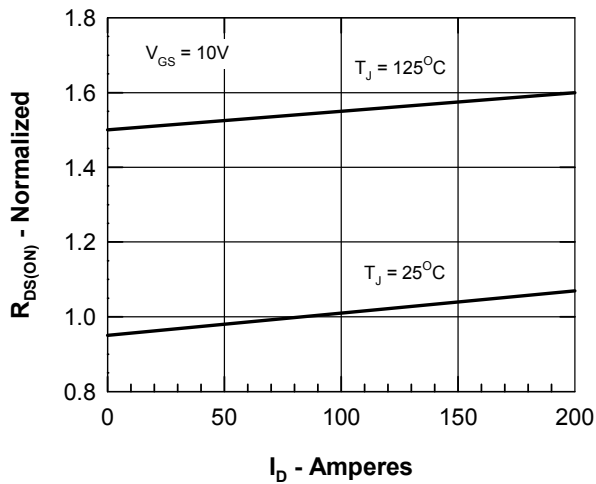


Figure 4. $R_{DS(on)}$ normalized to 15A/25°C vs. T_J

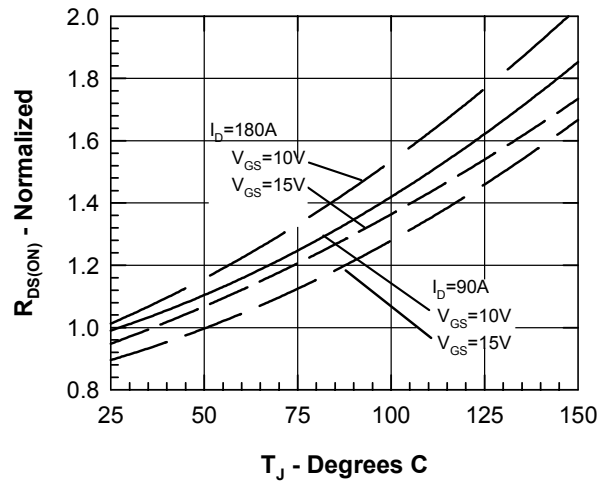


Figure 5. Drain Current vs. Case Temperature

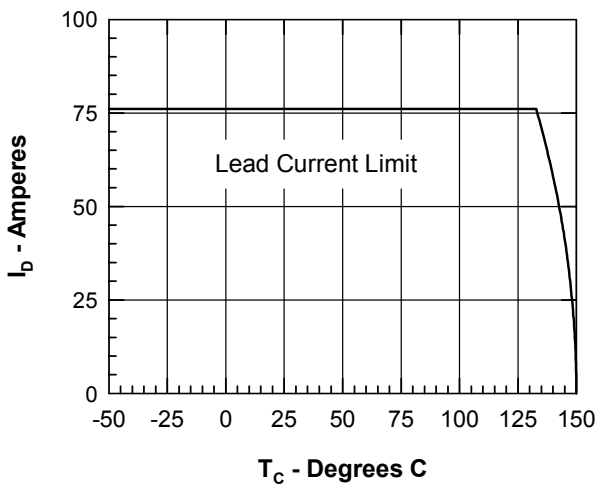


Figure 6. Admittance Curves

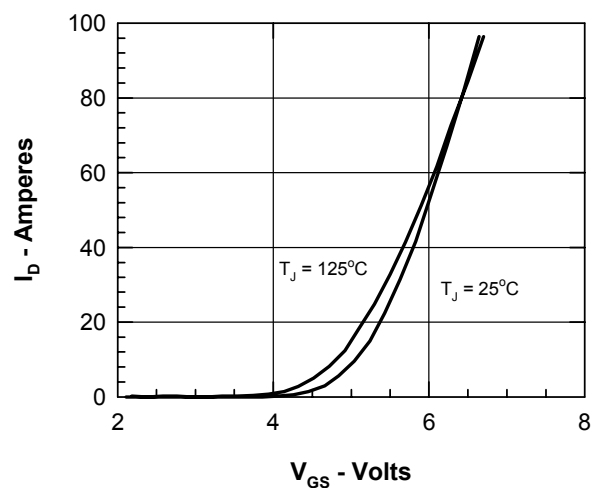


Figure 7. Gate Charge

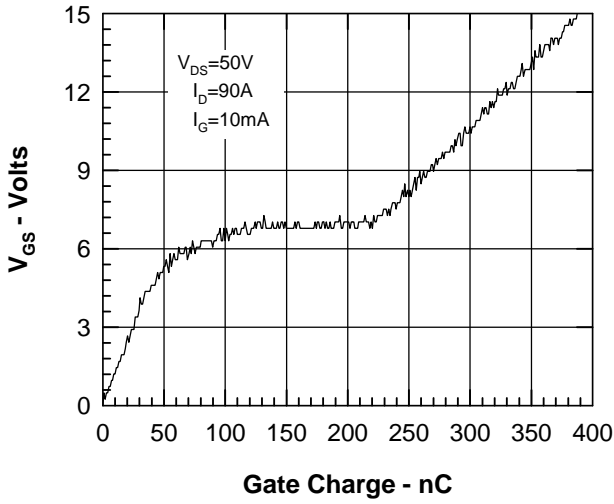


Figure 8. Capacitance Curves

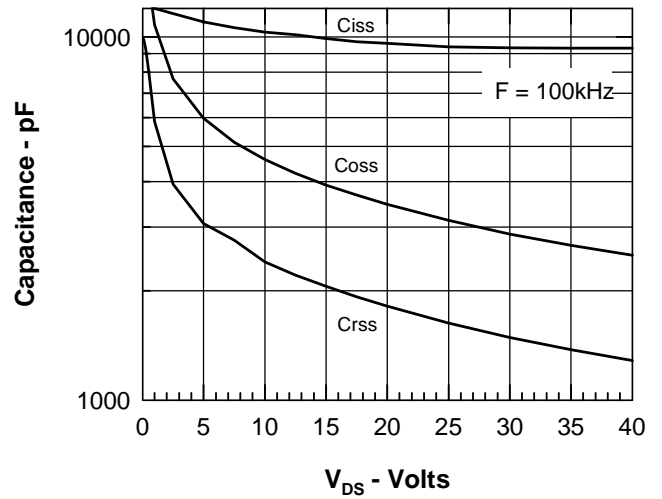


Figure 9. Forward Voltage Drop of the Intrinsic Diode

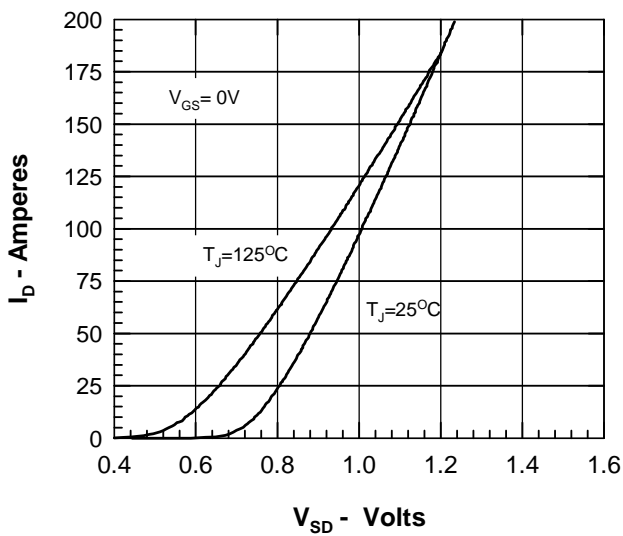


Figure 10. Forward Bias Safe Operating Area

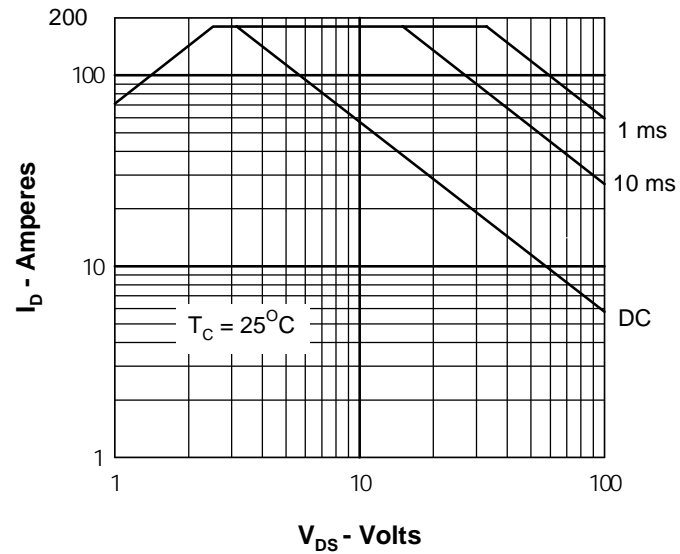


Figure 11. Transient Thermal Resistance

